

TRADEMARKS ONLY

To the Director of the U.S. Patent and Trademark Office: Please record the attached documents or the new address(es) below.

1. Name of conveying party(ies):
Avogy, Inc.
677 River Oaks Parkway
San Jose, CA 95134

Individual(s) Association
 General Partnership Limited Partnership
 Corporation-State: DE
 Other

Additional name(s) of conveying parties attached? Yes No

2. Name and address of receiving party(ies):
Additional name(s) of conveying parties attached? Yes No

Name: **Silicon Valley Bank**

Internal Address:

Street Address: **3003 Tasman Drive**

City: **Santa Clara**
State: **CA**
Country: **USA**
Zip: **95054**

3. Nature of conveyance/ Execution Date(s):

Execution Date(s): **March 21, 2014**

Assignment Merger
 Security Agreement Change of Name
 Other : **Release**

Association Citizenship
 General Partnership Citizenship
 Limited Partnership Citizenship
 Corporation Citizenship : **United States, CA**
 Other Citizenship

If assignee is not domiciled in the United States, a domestic representative designation is attached: Yes No
(Designations must be a separate document from assignment)

4. Application number(s) or registration number(s) and identification or description of the Trademark:

A. Trademark Serial No.(s)	B. Trademark Registration No.(s)
85/661149	

C. Identification or Description of Trademark(s) (and Filing Date if Application or Registration Number is unknown): Additional sheets attached? Yes No

5. Name and address of party to whom correspondence concerning document should be mailed:

Name: **UCC Direct Services**

Internal Address: **Attn: 14080632**

Street Address: **187 Wolf Road, Suite 101**

City: **Albany** State: **NY** ZIP: **12205**

Phone Number: **1-800-342-3676 X 4065**

Fax Number: **1-800-962-7049**

Email Address: **cls-udsalbany@wolterskluwer.com**

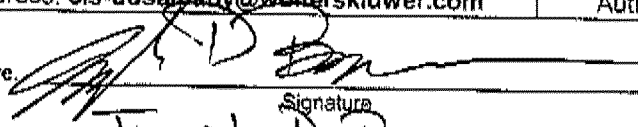
6. Total number of applications and registrations involved: **1**

7. Total fee (37 CFR 2.6 (b)(6) & 3.41): **\$40.00**
 Authorized to be charged by credit card
 Authorized to be charged to deposit account
 Enclosed

8. Payment Information:

a. Credit Card Last 4 Numbers **0974**
Expiration Date **3/17**

b. Deposit Account Number
Authorized User Name

9. Signature: 
Joseph D. Borgman
Name of Person Signing

Date: 3-31-14

Total number of pages including cover sheet, attachments, and document:

Documents to be recorded (including cover sheet) should be faxed to (571) 273-0140, or mailed to: Mail Stop Assignment Recordation Services, Director of the USPTO, P.O. Box 1450, Alexandria, VA 22304-1450

OP \$40.00 85661149

INTELLECTUAL PROPERTY SECURITY AGREEMENT

This Intellectual Property Security Agreement ("Agreement") is entered into as of the Effective Date by and between SILICON VALLEY BANK ("Bank") and AVOGY, INC. ("Grantor").

RECITALS

A. Bank has agreed to make certain advances of money and to extend certain financial accommodation to Grantor (the "Loans") in the amounts and manner set forth in that certain Loan and Security Agreement by and between Bank and Grantor dated the Effective Date (as the same may be amended, modified or supplemented from time to time, the "Loan Agreement"; capitalized terms used herein are used as defined in the Loan Agreement). Bank is willing to make the Loans to Grantor, but only upon the condition, among others, that Grantor shall grant to Bank a security interest in certain Copyrights, Trademarks, Patents, and Mask Works (as each term is described below) to secure the obligations of Grantor under the Loan Agreement.

B. Pursuant to the terms of the Loan Agreement, Grantor has granted to Bank a security interest in all of Grantor's right, title and interest, whether presently existing or hereafter acquired, in, to and under all of the Collateral.

NOW, THEREFORE, for good and valuable consideration, receipt of which is hereby acknowledged, and intending to be legally bound, as collateral security for the prompt and complete payment when due of its obligations under the Loan Agreement, Grantor hereby represents, warrants, covenants and agrees as follows:

AGREEMENT

1. Grant of Security Interest. To secure its obligations under the Loan Agreement, Grantor grants and pledges to Bank a security interest in all of Grantor's right, title and interest in, to and under its intellectual property (all of which shall collectively be called the "Intellectual Property Collateral"), including, without limitation, the following:

(a) Any and all copyright rights, copyright applications, copyright registrations and like protections in each work or authorship and derivative work thereof, whether published or unpublished and whether or not the same also constitutes a trade secret, now or hereafter existing, created, acquired or held, including without limitation those set forth on Exhibit A attached hereto (collectively, the "Copyrights");

(b) Any and all trade secrets, and any and all intellectual property rights in computer software and computer software products now or hereafter existing, created, acquired or held;

(c) Any and all design rights that may be available to Grantor now or hereafter existing, created, acquired or held;

(d) All patents, patent applications and like protections including, without limitation, improvements, divisions, continuations, renewals, reissues, extensions and continuations-in-part of the same, including without limitation the patents and patent applications set forth on Exhibit B attached hereto (collectively, the "Patents");

(e) Any trademark and servicemark rights, whether registered or not, applications to register and registrations of the same and like protections, and the entire goodwill of the business of Grantor

TRADEMARK

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connected with and symbolized by such trademarks, including without limitation those set forth on Exhibit C attached hereto (collectively, the "Trademarks");

(f) All mask works or similar rights available for the protection of semiconductor chips, now owned or hereafter acquired, including, without limitation those set forth on Exhibit D attached hereto (collectively, the "Mask Works");

(g) Any and all claims for damages by way of past, present and future infringements of any of the rights included above, with the right, but not the obligation, to sue for and collect such damages for said use or infringement of the intellectual property rights identified above;

(h) All licenses or other rights to use any of the Copyrights, Patents, Trademarks, or Mask Works and all license fees and royalties arising from such use to the extent permitted by such license or rights;

(i) All amendments, extensions, renewals and extensions of any of the Copyrights, Trademarks, Patents, or Mask Works; and

(j) All proceeds and products of the foregoing, including without limitation all payments under insurance or any indemnity or warranty payable in respect of any of the foregoing;

provided that, notwithstanding anything contained in this Agreement to the contrary, the term "Intellectual Property Collateral" shall not include: (i) any rights held under a license that are not assignable by their terms without the consent of the licensor thereof (but only to the extent such restriction on assignment is enforceable under applicable law), provided, however, that upon termination of such prohibition, such interest shall immediately become Intellectual Property Collateral without any action of Grantor or Bank and the exclusions of this clause (i) shall in no way be construed to limit, impair, or otherwise affect Bank's continuing security interests in and liens upon any rights or interests of Grantor in or to all accounts, license and royalty fees and other revenues, proceeds, or income arising out of or relating to any license or the foregoing intellectual property; and (ii) any United States intent-to-use trademark applications to the extent that, and solely during the period in which, the grant of a security interest therein would impair the validity or enforceability of such intent-to-use trademark applications under applicable federal law, provided that upon submission and acceptance by the United States Patent and Trademark Office of an amendment to allege use pursuant to 15 U.S.C. Section 1060(a) (or any successor provision), such intent-to-use trademark application shall be considered Intellectual Property Collateral.

2. Recordation. Grantor authorizes the Commissioner for Patents, the Commissioner for Trademarks and the Register of Copyrights and any other government officials to record and register this Agreement upon request by Bank.

3. Authorization. Grantor hereby authorizes Bank to (a) modify this Agreement unilaterally by amending the exhibits to this Agreement to include any Intellectual Property Collateral which Grantor obtains subsequent to the date of this Agreement, and (b) file a duplicate original of this Agreement containing amended exhibits reflecting such new Intellectual Property Collateral.

4. Loan Documents. This Agreement has been entered into pursuant to and in conjunction with the Loan Agreement, which is hereby incorporated by reference. The provisions of the Loan Agreement shall supersede and control over any conflicting or inconsistent provision herein. The rights and remedies of Bank with respect to the Intellectual Property Collateral are as provided by the Loan Agreement and related documents, and nothing in this Agreement shall be deemed to limit such rights and remedies.

5. Execution in Counterparts. This Agreement may be executed in counterparts (and by different parties hereto in different counterparts), each of which shall constitute an original, but all of which when taken together shall constitute a single contract. Delivery of an executed counterpart of a signature page to this Agreement by facsimile or in electronic (i.e., "pdf" or "tif" format) shall be effective as delivery of a manually executed counterpart of this Agreement.


6. Successors and Assigns. This Agreement will be binding on and shall inure to the benefit of the parties hereto and their respective successors and assigns.

7. Governing Law. This Agreement and any claim, controversy, dispute or cause of action (whether in contract or tort or otherwise) based upon, arising out of or relating to this Agreement and the transactions contemplated hereby and thereby shall be governed by, and construed in accordance with, the laws of the United States and the State of California, without giving effect to any choice or conflict of law provision or rule (whether of the State of California or any other jurisdiction).

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers thereunto duly authorized as of the first date written above.

GRANTOR:

AVOGY, INC.


By: DINESH GOPINATHAN
Title: CEO

BANK:

SILICON VALLEY BANK

By: _____
Title: _____

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers thereunto duly authorized as of the first date written above.

GRANTOR:

AVOGY, INC.

By: _____
Title: _____

BANK:

SILICON VALLEY BANK

Uli M. Maitra
By: MONA MITRA
Title: VICE PRESIDENT

EXHIBIT A

Copyrights

N/A

EXHIBIT B

Patents

FILE NO.	FAMILY NO.	CLIENT REF. NO.	TITLE	COUNTRY	APPLN. NO.	FILING DATE	PUB NO.	PUB DATE	PATENT NO.	ISSUE DATE	STATUS	INVENTORS
93444-81E757	0001000US	EPS00001	CONTROLLED DOPING IN THE V-MATERIALS	United States of America	13079710	4/4/11	US-2012-0248577-A1	10/4/12			Published	Linda T. Romano, Dave P. Bour, Erik C. Kizlyall, Hui Nie, Thomas R. Prunty
93444-81E760	0003000US	EPS00003	ELECTRICAL ISOLATION OF HIGH DIELECTRIC DENSITY REGIONS IN A SEMICONDUCTOR DEVICE	United States of America	13180738	7/12/11	US-2013-0015552-A1	1/17/13			Published	Erik C. Kizlyall, Dave P. Bour, Richard J. Brown, Andrew P. Edwards, Hui Nie, Linda Romano
93444-82E397	0004000US	EPS-00304	EDGE TERMINATION BY IONIMPLANTATION	United States of America	13391165	11/27/11	US-2013-0126888-A1				Published	Erik C. Kizlyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444-82E389	0005000US	EPS00005	ORGAN OPTIC SOURCE CONTACTS FOR VERTICAL POWER DEVICES	United States of America	13336192	12/14/11	US-2013-0153917-A1				Published	Linda Romano, Andrew P. Edwards, Dave P. Bour, Erik C. Kizlyall
93444-80E244	0006000US	EPS-00006	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REBROWN GATE	United States of America	13198655	8/4/11	US-2013-0032811-A1	2/7/13			Published	Erik C. Kizlyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444-84E593	0006100PC	EPS-00006PC	METHOD AND SYSTEM FOR A GAN VERTICAL JET UTILIZING A REBROWN GATE	PCT	PCT/US2012049549	8/3/12	WO 2013/020061	2/7/13			Published	Erik C. Kizlyall, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty

93444- 808236	0007801US	EP8- 0007	METHOD AND SYSTEM FOR A GAN VERTICAL JFET UTILIZING A REGROWN CHANNEL	United States of America	13198659	8/4/11	US-2013- 0032812-A1	27/13	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 846589	000710PC	EP8- 0007PC	METHOD AND SYSTEM FOR A GAN VERTICAL JFET UTILIZING A REGROWN CHANNEL	PCT	PCTUS1249520	8/3/12	WO 2013/020051	27/13	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 846593	000800PC	EP8- 0008PC	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	PCT	PCTUS2012048194	7/25/12	WO 2013/019521	27/13	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 808237	000800US	EP8- 0008	METHOD AND SYSTEM FOR DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	13198661	8/4/11	US-2013- 0032813-A1	27/13	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 808239	000900US	EP80009	METHOD AND SYSTEM FOR FORMATION OF P- N JUNCTIONS IN GALLIUM NITRIDE BASED ELECTRONICS	United States of America	13198666	8/4/11	US-2013- 0032814-A1	27/13	Published	David P. Bour, Thomas R. Prunty, Linda Romano, Andrew P. Edwards, Isik C. Kizilyalli, Hui Nie, Richard J. Brown, Mehmet M. Rafi
93444- 808243	001000US	EP80010	METHOD AND SYSTEM FOR LOCAL CONTROL OF DEFECT DENSITY IN GALLIUM NITRIDE BASED ELECTRONICS	United States of America	13225345	9/2/11	US-2013- 0036783-A1		Published	David P. Bour, Linda Romano, Thomas R. Prunty, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown

29444- 856390	001100PC	EP8- 011PC	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	PCT	PCTUS2012062728	10/31/12	W/O 2013/066967	Published	Isik C, Kizilyalli, Hui Nie, Andrew P, Edwards, Linda Romano, Dave P, Bour, Richard J, Brown, Thomas R, Prunty
29444- 813851	001100US	EP89011	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	United States of America	13289219	11/4/11	US-2013- 0112985-A1	Issued	Isik C, Kizilyalli, Hui Nie, Andrew P, Edwards, Linda Romano, Dave P, Bour, Richard J, Brown, Thomas R, Prunty
29444- 860166	001110US	EP8- 0011-1	MONOLITHICALLY INTEGRATED VERTICAL JET AND SCHOTTKY DIODE	United States of America	13935345	7/5/13		Pending	Isik C, Kizilyalli, Hui Nie, Andrew P, Edwards, Linda Romano, Dave P, Bour, Richard J, Brown, Thomas R, Prunty
29444- 813853	001200US	EP89012	MONOLITHICALLY INTEGRATED HEAT AND SCHOTTKY DIODE	United States of America	13267552	10/6/11	US-2013- 0087803-A1	Published	Kizilyalli Isik C, Nie Hui, Edwards Andrew P, Romano Linda, David P, Bour, Brown Richard J, Prunty Thomas R
29444- 816904	001300US	EP89013	METHOD AND SYSTEM FOR FLOATING GUARD RINGS IN GAN MATERIALS	United States of America	13270696	10/11/11	US-2013- 0087835-A1	Published	Andrew P, Edwards, Hui Nie, Isik C, Kizilyalli, Richard J, Brown, Dave P, Bour, Linda Romano, Thomas R, Prunty
29444- 837922	001400PC		METHOD AND SYSTEM FOR DIFFUSION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	PCT	PCTUS2012086101	9/19/12		Pending	Dave P, Bour, Richard J, Brown, Isik C, Kizilyalli, Thomas R, Prunty, Linda Romano, Andrew P, Edwards, Hui Nie, Madhava M, Saj

93444- 816905	001400US	EP90014	METHOD AND SYSTEM FOR DIFFUSION AND IMPLANTATION IN GALLIUM NITRIDE BASED DEVICES	United States of America	13240877	9/22/11	US-2013- 0075748-A1	3/28/13	Published	Dave P. Bour, Richard J. Brown, Isik C. Kizilyalli, Linda Prunty, Linda Romano, Andrew P. Edwards, Hui Nie, Matthew M. Ref
93444- 819244	001500US	EP9- 0015	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED P-I-N SCHOTTKY (MPSI) DIODE	United States of America	13276625	10/11/11	US-2013- 0087878-A1	4/11/13	Published	Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 851214	001510PC	EP9- 0015PC	METHOD OF FABRICATING A GAN MERGED P-I-N SCHOTTKY (MPSI) DIODE	PCT	PCTUS201259245	10/8/12	WQ 2013055629		Published	Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Linda Romano, Dave P. Bour, Richard J. Brown, Thomas R. Prunty
93444- 819311	001600US	EP90016	VERTICAL GAN-BASED METAL INSULATOR SEMICONDUCTOR HET	United States of America	13315705	12/9/11	US-2013- 0146885-A1	8/5/13	Issued	Richard J. Brown, Hui Nie, Andrew Edwards, Isik Kizilyalli, David Bour, Thomas Prunty, Linda Romano, Matthew Ref
93444- 819312	001700US	EP90017	GAN-BASED SCHOTTKY BARRIER DIODE WITH ALGAN SURFACE LAYER	United States of America	13300009	11/18/11	US-2013- 0126886-A1		Published	Richard J. Brown, Thomas R. Prunty, Dave P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano, Matthew M. Ref
93444- 819312	001800US	EP90018	GAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	United States of America	13309928	11/18/11	US-2013- 0127006-A1	6/6/14	Issued	Matthew Ref, Richard J. Brown, Thomas R. Prunty, David P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano

93444-819131	001801US	EP-S-	CAN-BASED SCHOTTKY BARRIER DIODE WITH FIELD PLATE	United States of America	14062724	10/24/13	US-2014-0051236-A1	Published	Machan Raj, Richard J. Brown, Thomas R. Prunty, David P. Bour, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Linda Romano
93444-819134	001900US	EP-S0019	IN-SITU SiN GROWTH TO ENABLE SCHOTTKY CONTACT FOR GAN DEVICES	United States of America	13112055	12/6/11	US-2013-0143392-A1	Published	Linda Romano, Dave P. Bour, Andrew P. Edwards, Hui Nie, Isik C. Kizilyalli, Richard J. Brown, Thomas R. Prunty
93444-819135	002000US	EP-S0020	ALUMINUM GALLIUM NITRIDE ETC STOP LAYER FOR GALLIUM NITRIDE BASES DEVICES	United States of America	13299227	11/17/11	US-2013-0126684-A1	Published	Linda Romano, Andrew P. Edwards, Richard J. Brown, Dave P. Bour, Hui Nie, Isik C. Kizilyalli, Thomas R. Prunty, Mahesh M. Raj
93444-857908	002010US	EP-S-0020-1	ALUMINUM GALLIUM NITRIDE ETC STOP LAYER FOR GALLIUM NITRIDE BASED DEVICES	United States of America	13932290	7/1/13		Pending	Linda Romano, Andrew P. Edwards, Richard J. Brown, David P. Bour, Hui Nie, Isik C. Kizilyalli, Thomas R. Prunty, Mahesh Raj
93444-857908	002100PC	EP-S-0021PC	METHOD AND SYSTEM FOR A GAN SELF-ALIGNED VERTICAL MESFET	PCT	PCTUS2012065994	11/20/12	WO 2013095847	Published	Richard J. Brown, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Dave P. Bour
93444-857920	002100US	EP-S-0021	METHOD AND SYSTEM FOR A GAN SELF-ALIGNED VERTICAL MESFET	United States of America	13335572	12/22/11	US-2013-0161635-A1	Published	Richard J. Brown, Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Dave P. Bour
93444-859134	002200PC	EP-S-0022PC	METHOD OF FABRICATING A GALLIUM NITRIDE P-LIN PRODS USING IMPLANTATION	PCT	PCTUS2012068972	12/11/12	WO 2013096013	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Deany
93444-819136	002200US	EP-S-0022	METHOD OF FABRICATING A GAN P-EN DIODE USING IMPLANTATION	United States of America	13335529	12/22/11	US-2013-0161780-A1	Published	Isik C. Kizilyalli, Hui Nie, Andrew P. Edwards, Richard J. Brown, Donald R. Deany

93444-824393	002380US	EP80023	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	13907108	11/30/11	US-2013-013723-A1	8569153	10/29/13	Issued	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Erik C. Kizlyelli, Hai Nie
93444-821183	002310US	EP8-071-1	METHOD AND SYSTEM FOR CARBON DOPING CONTROL IN GALLIUM NITRIDE BASED DEVICES	United States of America	14061741	10/23/13				Pending	David P. Bour, Thomas R. Prunty, Linda Romano, Richard J. Brown, Erik C. Kizlyelli, Hai Nie
93444-854261	002400PC	EP8-0024PC	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	PCT	PCTUS201259250	10/8/12	W/O 2013/055631			Published	Andrew P. Edwards, Hai Nie, Erik C. Kizlyelli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
93444-822319	002400US	EP-0024	SCHOTTKY DIODE WITH BURIED LAYER IN GAN MATERIALS	United States of America	13270641	10/11/11	US-2013-098789-A1		4/11/13	Published	Andrew P. Edwards, Hai Nie, Erik C. Kizlyelli, Richard J. Brown, David P. Bour, Linda Romano, Thomas R. Prunty
93444-856389	002500PC	EP8-0025PC	METHOD AND SYSTEM FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	PCT	PCTUS2012062717	10/31/12	W/O 2013/074291			Published	Donald R. Disney, Andrew P. Edwards, Hai Nie, Richard J. Brown, Erik C. Kizlyelli, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444-823950	002500US	EP8-0025	METHOD AND SYSTEM FOR FABRICATING FLOATING GUARD RINGS IN GAN MATERIALS	United States of America	13299254	11/17/11	US-2013-0126805-A1			Allowed	Donald R. Disney, Andrew P. Edwards, Hai Nie, Richard J. Brown, Erik C. Kizlyelli, Dave P. Bour, Linda Romano, Thomas R. Prunty
93444-824394	002600US	EP80026	FABRICATION OF FLOATING GUARD RINGS USING SELECTIVE REGROWTH	United States of America	13334335	12/22/11	US-2013-0164893-A1	8592298	11/26/13	Issued	Linda Romano, David P. Bour, Andrew Edwards, Hai Nie, Erik C. Kizlyelli, Richard J. Brown, Thomas R. Prunty

93444-824395	002700US	EPS-0027	VERTICAL GAN JET WITH GATE SOURCE ELECTRODES ON REGROWN GATE	United States of America	1315720	12/9/11	US-2013-0146886-A1	Allowed	Donald R. Disney, Hui Nie, Isik C. Kizilyalli, Richard J. Brown
93444-827888	002710PC	EPS-0027PC	VERTICAL GAN JET WITH GATE AND SOURCE ELECTRODES ON REGROWN GATE	PCT	PCTUS2012066669	11/27/12	WO 2013/085748	Published	Donald R. Disney, Hui Nie, Isik C. Kizilyalli, Richard J. Brown
93444-827872	002800PC	EPS-0028PC	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	PCT	PCTUS2012069251	12/12/12	WO 2013/096034	Published	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Isik C. Kizilyalli
93444-826392	002800US	EPS-0028	METHOD AND SYSTEM FOR JUNCTION TERMINATION IN GAN MATERIALS USING CONDUCTIVITY MODULATION	United States of America	1334742	12/22/11	US-2013-0161633-A1	Allowed	Hui Nie, Andrew P. Edwards, Donald R. Disney, Richard J. Brown, Isik C. Kizilyalli
93444-826381	002900US	EPS-0029	METHOD AND SYSTEM FOR PLANAR REGROWTH IN GAN ELECTRONIC DEVICES	United States of America	13445812	5/7/12	US-2013-0292686-A1	Published	Isik C. Kizilyalli, Linda Romano, Dave P. Bohr
93444-859133	003000PC	EPS-0030PC	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF-ALIGNED SOURCE AND GATE	PCT	PCTUS2012069299	12/12/12	WO 2013/096062	Published	Donald R. Disney, Isik C. Kizilyalli, Hui Nie, Linda Romano, Richard J. Brown, Madhan M. Raj
93444-826380	003000US	EPS-0030	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF-ALIGNED SOURCE AND GATE	United States of America	13334514	12/22/11	US-2013-0161705-A1	Published	Donald R. Disney, Isik C. Kizilyalli, Hui Nie, Linda Romano, Richard J. Brown, Madhan M. Raj
93444-826379	003100US	EPS-0031	METHOD AND SYSTEM FOR FABRICATING EDGE TERMINATION STRUCTURES IN GAN MATERIALS	United States of America	13335383	12/22/11	US-2013-0161634-A1	Allowed	Donald R. Disney, Isik C. Kizilyalli, Linda Romano, Andrew P. Edwards, Hui Nie
93444-833448	003200US	EPS-0032	GAN VERTICAL SUPERJUNCTION DEVICE STRUCTURES AND FABRICATION METHODS	United States of America	13529822	6/21/12	US-2013-0341677-A1	Published	Hui Nie, Andrew P. Edwards, Donald R. Disney, Isik C. Kizilyalli

93444- 833463	003300US	EP8- 0033	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL JET WITH SELF-ALIGNED GATE METALLIZATION	United States of America	13468325	5/10/12	US-2013-0299873-A1	Allowed	Donald R. Disney, Richard J. Brown, Hui Nie
93444- 839418	003310US	EP8- 0033.1	METHOD AND SYSTEM FOR A GAN VERTICAL JET WITH SELF-ALIGNED SOURCE METALLIZATION	United States of America	13468332	5/10/12	EP-2013-0299882-A1	Allowed	Donald R. Disney, Richard J. Brown, Hui Nie
93444- 833463	003400US	EP8- 0034	VERTICAL GAN JET WITH LOW GATE DRAIN CAPACITANCE AND HIGH GATE SOURCE CAPACITANCE	United States of America	13675694	11/13/12		Pending	Donald R. Disney
93444- 840540	003300US	EP8- 0035	GAN POWER DEVICE WITH SOLIDIFIABLE BACKMETAL	United States of America	13552365	7/8/12	US-2014-0021479-A1	Published	Patrick James Lesko Hyzard, Brian Alvarez, Donald R. Disney
93444- 883361	003600PC	EP8- 0036-PC	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	PCT	PCTUS2013053702	6/6/13	WO 2014/025722	Published	Hui Nie, Donald R. Disney, Erik C. Kozlyell
93444- 840541	003600US	EP8- 0036	METHOD AND SYSTEM FOR GALLIUM NITRIDE ELECTRONIC DEVICES USING ENGINEERED SUBSTRATES	United States of America	13572408	8/10/12	US-2014-0062447-A1	Published	Hui Nie, Donald R. Disney, Erik C. Kozlyell
93444- 840542	003700US	EP8- 0037	METHOD AND SYSTEM FOR EDGE TERMINATION IN GAN MATERIALS BY SELECTIVE AREA IMPLANTATION DOPING	United States of America	13586330	8/15/12	US-2014-0098903-A1	Published	Andrew Edwards, Hui Nie, Erik C. Kozlyell, Dave Bour
93444- 883362	003800PC	EP8- 0038-PC	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED JAIN SCHOTKY (MFS) DIODE BY REGROWTH AND ETCH BACK	PCT	PCTUS2013053751	6/6/13		Pending	Madhavi M. Raj, Brian Alvarez, Dave P. Bour, Andrew P. Edwards, Hui Nie, Erik C. Kozlyell

93444- 840543	003800US	EP8- 0038	METHOD OF FABRICATING A GALLIUM NITRIDE MERGED PLAN SCHOTTKY (MES) DIODE BY REGROWTH AND PICH BACK BONDABLE TOP METAL CONTACTS FOR GALLIUM NITRIDE POWER DEVICES	United States of America	13585121	8/3/4/12	US-2014- 0046302-A1	Published	Medhane M. Raj, Brian Alvarez, Dave P. Bour, Andrew P. Edwards, Hui Nig, Jalk C. Kizilyalli
93444- 833972	003900US	EP8- 0039	AC-DC CONVERTER FOR WIDE RANGE OUTPUT VOLTAGE AND HIGH SWITCHING FREQUENCY	United States of America	13614467	9/3/2/12		Pending	Brian Joel Alvarez, Donald R. Denny, Hui Nig, Patrick James Lazo Hyand
93444- 843971	004000US	EP8- 0040	METHOD AND SYSTEM FOR IN-SITU AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	United States of America	13692717	12/3/12		Pending	Stethipong Angkatsarakul, Hermal N. Shah
93444- 843980	004100US	EP8- 0041	METHOD AND SYSTEM FOR IN-SITU AND REGROWTH IN GALLIUM NITRIDE BASED DEVICES	United States of America	13571743	8/16/12	US-2014- 0045306-A1	Published	David P. Bour, Thomas R. Prunty, Hui Nig, Madhan M. Raj
93444- 851061	004200US	EP8- 0042	GAN VERTICAL BIPOLAR TRANSISTOR	United States of America	13675916	11/13/12		Pending	Hui Nig, Andrew P. Edwards, Jalk C. Kizilyalli, Dave Bour
93444- 851060	004300US	EP8- 0043	METHOD AND SYSTEM FOR GALLIUM NITRIDE VERTICAL JFET WITH SEPARATED GATE AND SOURCE	United States of America	13689574	11/29/12		Pending	Hui Nig, Andrew P. Edwards, Dave P. Bour, Jalk C. Kizilyalli, Richard J. Brown, Thomas R. Prunty
93444- 892931	004400PC	EP8- 0044	LATERAL GAN JFET WITH VERTICAL DRIFT REGION	PCT	PCTUS2013069469	11/11/13		Pending	Hui Nig, Andrew Edwards, Jalk Kizilyalli, Dave Bour, Thomas R. Prunty
93444- 851039	004400US	EP8- 0044	LATERAL GAN JFET WITH VERTICAL DRIFT REGION	United States of America	13675826	11/13/12		Pending	Hui Nig, Andrew P. Edwards, Jalk Kizilyalli, Dave Bour, Thomas R. Prunty
93444- 854149	004500PC	EP8- 0045-PC	HIGH POWER DENSITY OFF-LINE POWER SUPPLY	PCT	PCTUS2013071522	11/22/13		Pending	Hermal N. Shah
93444- 851038	004500US	EP8- 0045	HIGH POWER DENSITY OFF-LINE POWER SUPPLY	United States of America	13731872	12/31/12		Pending	Hermal N. Shah

93444-835613	004600PC	EP5-0046-PC	GALLIUM NITRIDE VERTICAL JET WITH HEXAGONAL CELL STRUCTURE	PCT	PCTUS2013076007	12/18/13	Pending	Andrew P. Edwards, Hai Nig, Donald R. Disney, Isik C. Kizilyalli
93444-8356292	004600US	EP5-0046	GALLIUM NITRIDE VERTICAL JET WITH HEXAGONAL CELL STRUCTURE	United States of America	13735897	1/7/13	Pending	Andrew P. Edwards, Hai Nig, Donald R. Disney, Isik C. Kizilyalli
93444-8356301	004700US	EP5-0047	METHOD AND SYSTEM FOR CO-PACKAGING GALLIUM NITRIDE ELECTRONICS	United States of America	13730619	12/28/12	Pending	Donald R. Disney, Heman N. Shah
93444-835614	004803PC	EP5-0048-PC	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	PCT	PCTUS2013076009	12/18/13	Pending	Hai Nig, Andrew P. Edwards, Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Quentin Diduck
93444-8356302	004800US	EP5-0048	METHOD AND SYSTEM FOR A GALLIUM NITRIDE VERTICAL TRANSISTOR	United States of America	13735912	1/7/13	Pending	Hai Nig, Andrew P. Edwards, Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Quentin Diduck
93444-8356302	004900US	EP5-0049	VERTICAL GAN POWER DEVICE WITH BREAKDOWN VOLTAGE CONTROL	United States of America	13721562	12/20/12	Pending	Donald R. Disney
93444-8356165	005000US	EP5-0050	GALLIUM NITRIDE FIELD EFFECT TRANSISTOR WITH BURIED FIELD FLATE PROTECTED LATERAL CHANNEL	United States of America	14077039	11/11/13	Pending	Ozgur Akas, Isik C. Kizilyalli
93444-8356147	005200US	EP5-0052	METHOD OF FABRICATING A MERGED PN JUNCTION AND SCHOTTKY DIODE WITH REGROWN GALLIUM NITRIDE LAYER	United States of America	13866286	4/19/13	Pending	Isik C. Kizilyalli, Dave P. Bour, Thomas R. Prunty, Hai Nig, Quentin Diduck, Ozgur Akas
93444-8735690	005300US	EP5-0053	METHOD AND SYSTEM FOR CO-PACKAGING VERTICAL GALLIUM NITRIDE POWER DEVICES	United States of America	13901546	5/23/13	Pending	Donald R. Disney, Heman N. Shah

93444- 823691	005400US 0054	EP8- 0054	METHOD AND SYSTEM FOR OPERATING GALLIUM NITRIDE ELECTRONICS	United States of America	14065708	10/3/13	Pending	Hemal N. Shah, Donald R. Disney, Harald Amiridhani Nemagendi
93444- 873610	005500US 0055	EP8- 0055	HIGH POWER GALLIUM NITRIDE ELECTRONICS USING MISCELLI SUBSTRATES	United States of America	14071032	11/4/13	Pending	Isk C. Kizilyalli, David P. Hoyer, Thomas R. Prunty, Gangdong Ye
93444- 880156	005600US 0056	EP8- 0056	AC-DC CONVERTER WITH ADJUSTABLE OUTPUT	United States of America	14095759	12/3/13	Pending	Hemal N. Shah, Vinod Khosla
93444- 880156	005700US 0057	EP8- 0057	METHOD AND SYSTEM FOR INTERLEAVED BOOST CONVERTER WITH CO-PACKAGED GALLIUM NITRIDE POWER DEVICES	United States of America	14083217	11/18/13	Pending	Hemal N. Shah, Donald R. Disney

EXHIBIT C

Trademarks

Pending Applications

Mark	Country	Serial No.	Filing Date
TRUE GAN	Australia (Madrid Protocol)	1533372	11/19/12
TRUE GAN	Singapore (Madrid Protocol)	T1219939A	11/19/12
TRUE GAN	Switzerland (Madrid Protocol)	1141080	11/19/12
TRUE GAN	United States	85/661149	06/25/12
TRUE GAN	Vietnam (Madrid Protocol)	1141080	11/19/12

Issued Registrations

Mark	Country	Reg. No.	Reg. Date
TRUE GAN	China (Madrid Protocol)	1141080	11/19/12
TRUE GAN	European Community (Madrid Protocol)	1141080	11/19/12
TRUE GAN	Madrid Protocol	1141080	11/19/12
TRUE GAN	Japan (Madrid Protocol)	1141080	11/19/12
TRUE GAN	Korea (Madrid Protocol)	1141080	11/19/12

EXHIBIT D

Mask Works

N/A